

# BRC5N50ZC

Rev.A Jul.-2024

PDFN5×6 N

N-Channel MOSFET in a PDFN5×6 Plastic Package.

$V_{DS}(V)=500V$   $I_D=3A$

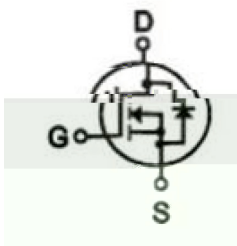
$R_{DS(ON)}@10V<1.6$  (Typ. 1.5 )

$R_{DS(ON)}@6V<2.0$  (Typ. 1.6 )

HF Product.

## LED

Used in high-frequency switching power supply, electronic ballast, LED power supply and high-speed air duct.



## / Absolute Maximum Ratings(Ta=25 )

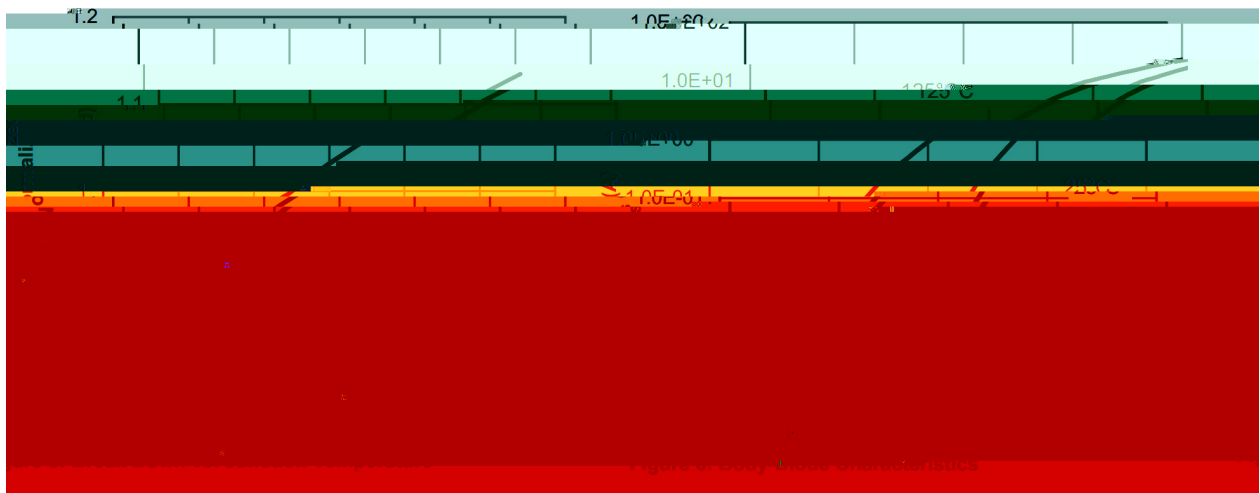
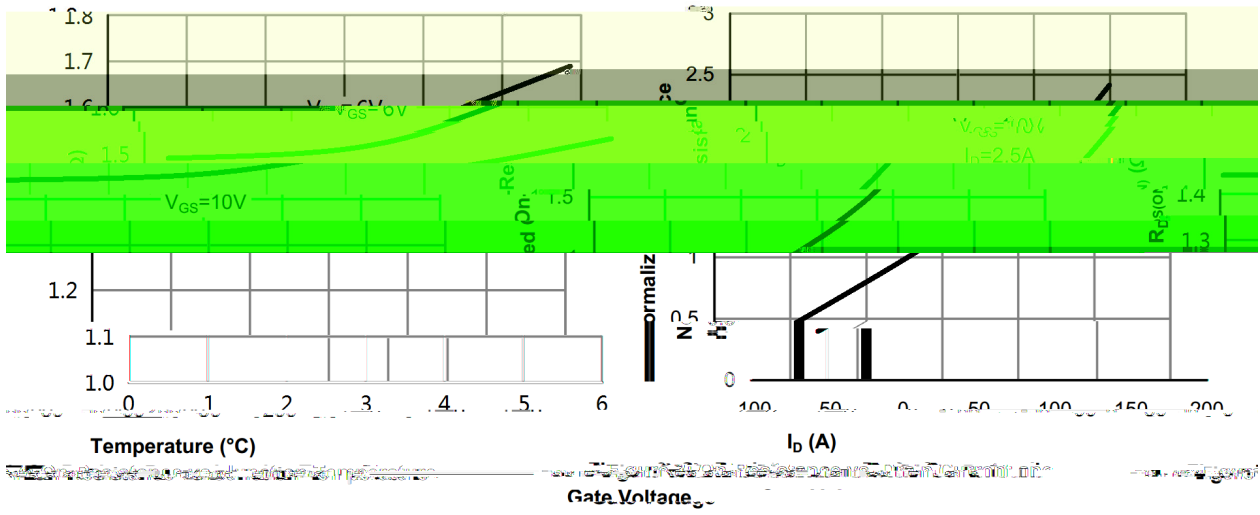
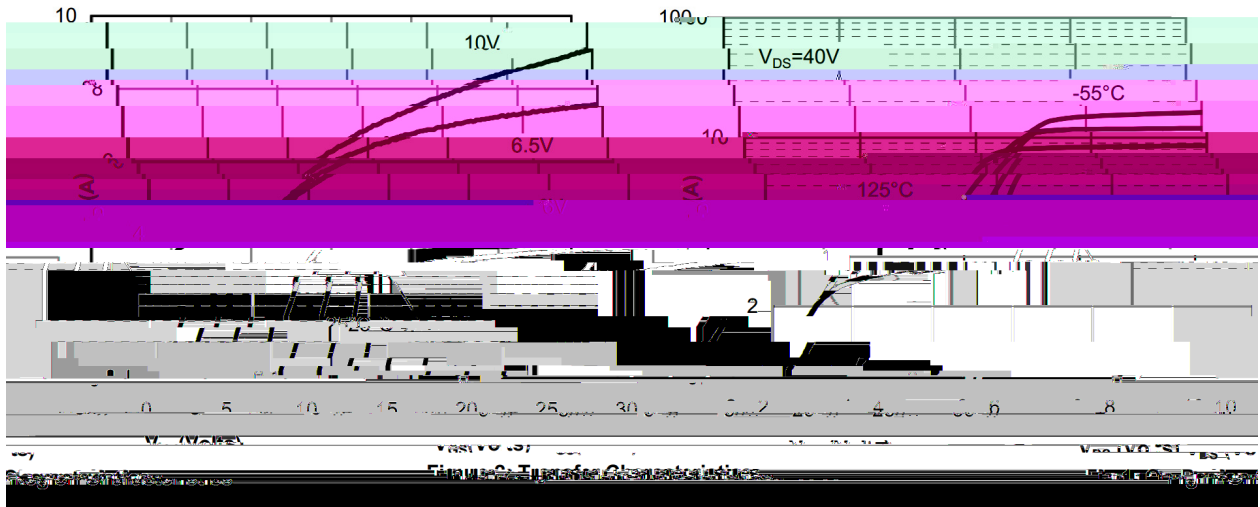
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	500	V
Drain Current	$I_D(T_C=25)$	3	A
Drain Current - Pulsed	$I_{DM}$	9.2	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Avalanche Current	$I_{AR}$	7	A
Single Pulsed Avalanche Energy	$E_{AS}$	218	mJ
Power Dissipation (Tc=25 )	$P_D$	33	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	
Thermal resistance,Junction to Case	$R_{\theta JC}$	3.79	/ W

## / Electrical Characteristics(Ta=25 )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	500	560		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=500V$ $V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 30V$ $V_{DS}=0V$			$\pm 0.1$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2	3.2	4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.5A$		1.5	1.6	
	$R_{DS(on)}$	$V_{GS}=6V$ $I_D=1A$		1.6	2.0	
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		570		pF
Output Capacitance	$C_{oss}$			150		pF
Reverse Transfer Capacitance	$C_{rss}$			10		pF
Total Gate Charge	$Q_G$	$V_{DS}= 400V,$ $I_D= 5.0A,$ $V_{GS}= 10V$		25		nC
Gate-Source Charge	$Q_{GS}$			6		
Gate-Drain Charge	$Q_{GD}$			8		



/ Electrical Characteristic Curve



**/ Electrical Characteristic Curve**

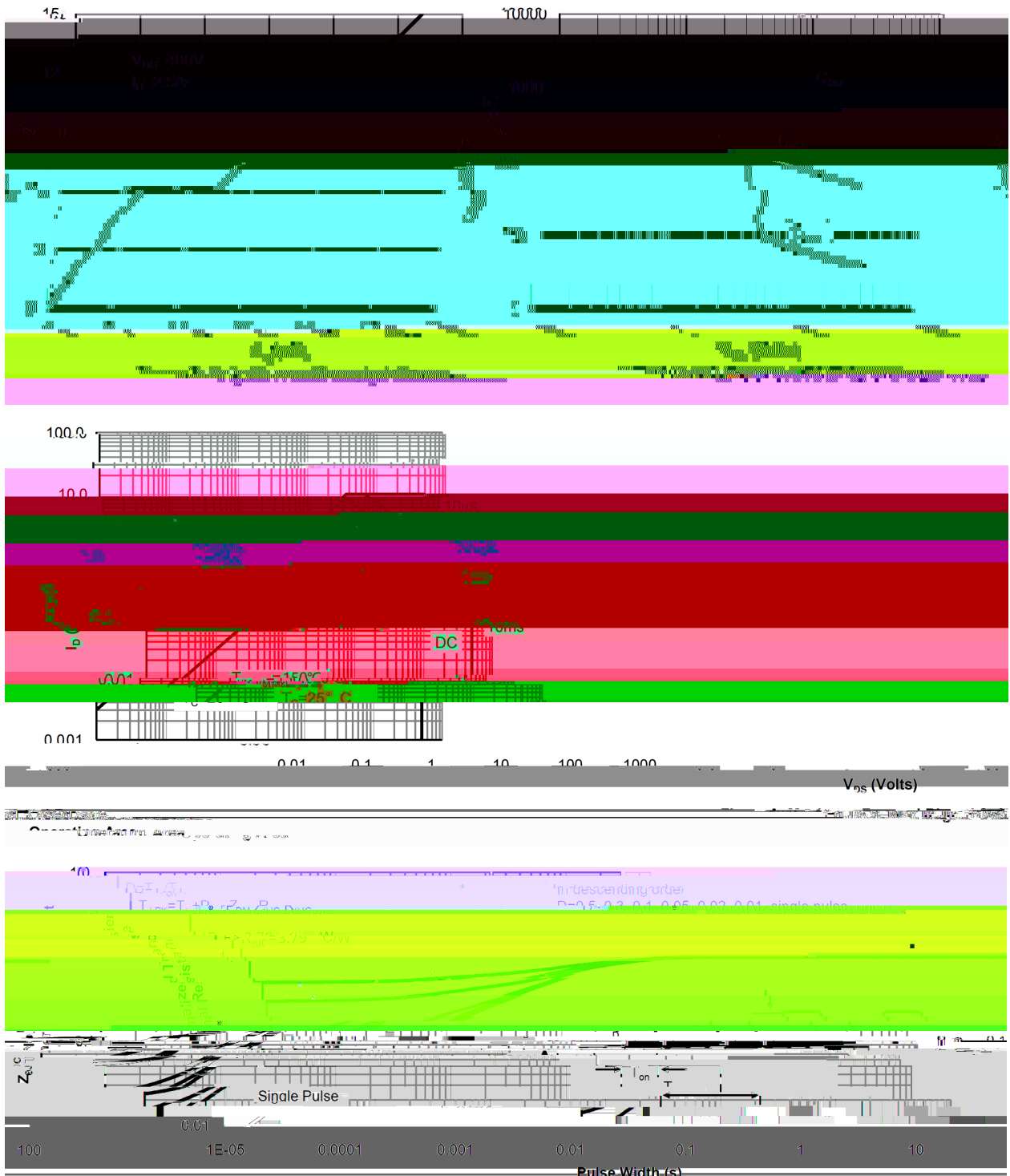


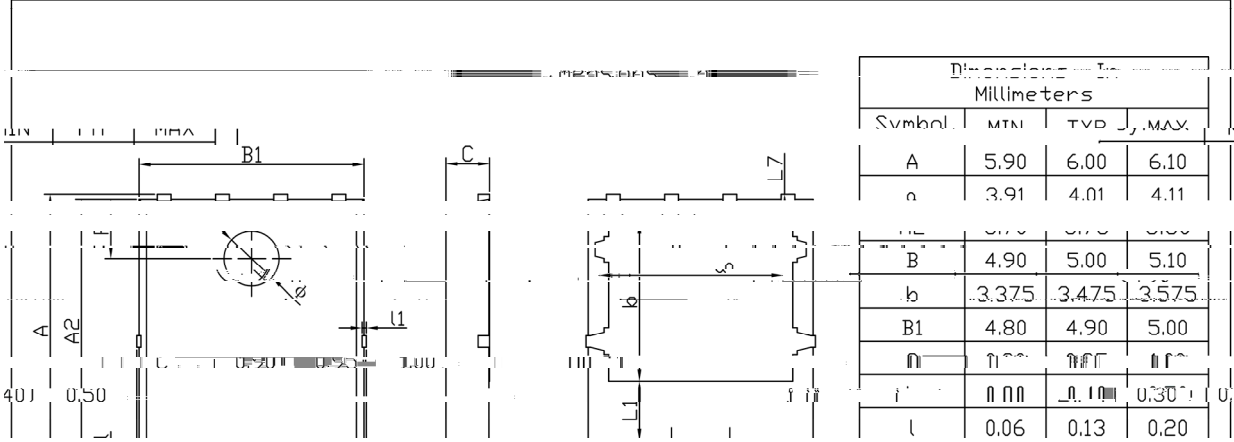
Figure 10: Normalized Maximum Transient Thermal Impedance

**/ Package Dimensions**

B

PDFN5 X6

Unit:mm



/ Marking Instructions



BR  
5N50  
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Note  
5N50

